

In the Claims:

1. (Currently Amended) A polishing pad useful for planarizing a surface of a semiconductor device or a precursor thereto, ~~said~~the pad comprising:
a polishing layer for planarizing ~~said~~the surface, ~~said~~the polishing layer having:
 - i. a hardness of about 40-70 Shore D;
 - ii. a tensile Modulus of about 150 – 2,000 MPa at 40°C;
 - iii. a KEL of about 100-1,000 (1/Pa at 40°C); and
 - iv. an E' ratio at 30°C-90°C of about 1-4.6.
2. (Currently Amended) ~~A~~The polishing pad in accordance with Claim 1, wherein ~~said~~the pad ~~being~~is an elongated sheet, a belt or a disk.
3. (Currently Amended) ~~The~~A polishing pad in accordance with Claim 1, wherein ~~said~~the pad further ~~comprising~~comprises at least one non-polishing layer.
4. (Currently Amended) ~~A~~The polishing pad in accordance with Claim 1, wherein the polishing layer further comprises a macro-texture having an average dimension of greater than a micron and a micro-texture comprising a plurality of asperities with an average protrusion length of less than 0.5 microns.
5. (Currently Amended) ~~A~~The polishing pad in accordance with Claim 1, wherein ~~said~~the polishing layer ~~comprising~~comprises a thermoplastic polymer.
6. (Currently Amended) ~~A~~The polishing pad in accordance with Claim 1, wherein ~~said~~the polishing layer ~~comprising~~comprises a thermoset polymer.
7. (Currently Amended) ~~A~~The polishing pad in accordance with Claim 1, wherein ~~said~~the polishing layer ~~being~~is non-porous.
8. (Currently Amended) ~~A~~The polishing pad in accordance with Claim 1, wherein ~~said~~the polishing layer ~~being~~is porous.

9. (Currently Amended) A ~~The~~ polishing pad in accordance with Claim 1, wherein
~~said~~the polishing layer ~~comprising~~comprises a filler.
10. (Currently Amended) A ~~The~~ polishing pad in accordance with Claim 1, wherein
~~said~~the polishing layer ~~being is devoid~~is devoid of a filler.
11. (Currently Amended) A ~~The~~ polishing pad in accordance with Claim 1, wherein
the polishing layer is about 500 to about 2600 microns thick.
12. (Currently Amended) A ~~The~~ polishing pad in accordance with Claim 1, wherein
the polishing layer has a surface roughness of from about one to about nine
micron Ra.
13. (Currently Amended) A ~~The~~ polishing pad in accordance with Claim 1, wherein
~~said~~the pad ~~having~~has a belt configuration and ~~comprising~~the polishing layer
comprises a thermoplastic polyurethane.
14. (Currently Amended) A ~~The~~ polishing pad in accordance with Claim 1, wherein
~~said~~the pad ~~having~~has a molded belt configuration.
15. (Currently Amended) A ~~The~~ polishing pad in accordance with Claim 1, wherein
the pad comprises ~~comprising~~ abrasive particles.
16. (Currently Amended) A ~~The~~ polishing pad in accordance with Claim 1, wherein
~~said~~the pad is devoid of abrasive particles.
17. (Currently Amended) A ~~The~~ polishing pad in accordance with Claim 1, wherein
at least a portion of ~~said~~the pad is transparent to electromagnetic radiation having
a wavelength of from about 190 to about 3500 nanometers.
18. (Currently Amended) A ~~The~~ polishing pad in accordance with Claim 1, wherein a
polishing surface of the pad has a surface roughness of about 1 to about 9 ~~micron~~
microns Ra and ~~an~~ the ratio of E' at from 30°C to 90°C is from about 1 to about
3.6.

19. (Currently Amended) ~~A~~ The polishing pad in accordance with claim 1, wherein ~~said~~ the polishing layer has a KEL in the range of about 125-850 (1/Pa at 40°C).
20. (Currently Amended) ~~A~~ The polishing pad in accordance with claim 1, wherein the polishing layer has the following:
 - a surface roughness of 2-7 ~~micron~~ microns Ra,
 - ~~a~~ hardness of about 45-65 Shore D,
 - ~~a~~ tensile modulus of about 150 – 1,500 MPa at 40°C,
 - ~~a~~ KEL of about 125-850 (1/Pa at 40°C), and
 - ~~a~~ E' ratio at 30°C-90°C of about 1.0-4.0.
21. (Currently Amended) ~~A~~ The polishing pad in accordance with claim 1, wherein the polishing layer has the following:
 - a surface roughness of 3-5 ~~micron~~ microns Ra,
 - ~~a~~ hardness of about 55-63 Shore D,
 - ~~a~~ tensile modulus of about 200 – 800 MPa at 40°C,
 - ~~a~~ KEL of about 150-400 (1/Pa at 40°C), and
 - ~~a~~ E' ratio at 30°C-90°C of about 1.0-3.5.
22. (Currently Amended) ~~A~~ The polishing pad in accordance with Claim 1, wherein the polishing layer comprises a polyurethane.
23. (Currently Amended) ~~A~~ The polishing pad in accordance with Claim 1, wherein the surface comprises a metal ~~which~~ that comprises copper.
24. (Currently Amended) ~~A~~ The polishing pad in accordance with Claim 1, wherein the surface comprises a metal ~~which~~ that comprises tungsten.
25. (Currently Amended) ~~A~~ The polishing pad in accordance with Claim 1, wherein the surface comprises a metal ~~which~~ that comprises aluminum.
26. (Currently Amended) The polishing pad of claim 22, ~~wherein in which~~ the polyurethane is a polyether based polyurethane.

27. (Currently Amended) The polishing pad of claim 22, wherein ~~in which~~ the polyurethane is a polyester based polyurethane.

28 to 52 (Cancelled).